SGS-THOMSON MICROELECTRONICS

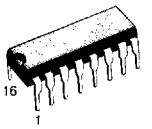
S G S-THOMSON

M54HC75
M74HC75

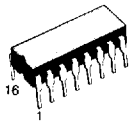
T-46-07-09

4-BIT D-TYPE LATCH

- HIGH SPEED
  t_{PD} = 15 ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION
  I_{CC} = 2 μA (MAX.) at T_A = 25°C
- HIGH NOISE IMMUNITY
  $V_{NIH} = V_{NIL}$ = 28% V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
  10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
  $|I_{OH}| = I_{OL}$ = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS
  $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
  V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE
  WITH 54/74LS75



B1N
Plastic Package



F1
Ceramic Frit Seal Package

M1
Micro Package

C1
Plastic Chip Carrier

ORDERING NUMBERS:

M54HC75 F1
M74HC75 B1N
M74HC75 F1
M74HC75 C1
M74HC75 M1

DESCRIPTION

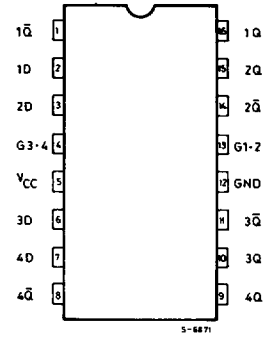
The M54/74HC75 is a high speed CMOS 4-BIT D-TYPE LATCH fabricated in silicon gate C²MOS technology.
It has the same high speed performance of LSTTL combined with true CMOS low power consumption. It contains two groups of 2-bit latches controlled by an enable input (G1 • 2 or G3 •4). These two latch groups can be used in different circuits. Each latch has Q and $\overline{Q}$ outputs (1Q - 4Q and $1\overline{Q}$ - $4\overline{Q}$). The data applied to the data input is transfered to the Q and $\overline{Q}$ outputs when the enable input is taken high and the outputs will follow the data input as long as the enable input is kept high. When the enable input is taken low, the information data applied to the data input is retained at the outputs. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

TRUTH TABLE

INPUTS		OUTPUTS		FUNCTION
D	G	Q	$\overline{Q}$	
L	H	L	H	—
H	H	H	L	—
X	L	Qn	$\overline{Q}$n	LATCH

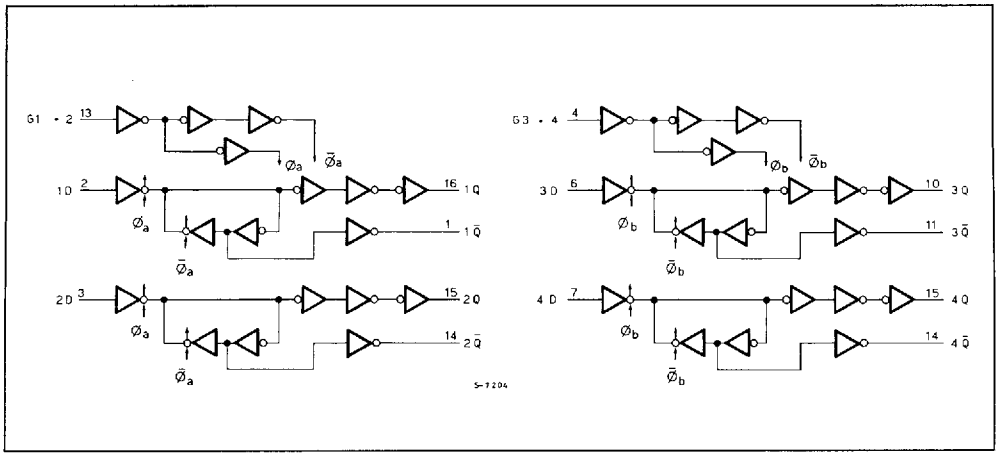
X: DON'T CARE

PIN CONNECTIONS (top view)



FOR CHIP CARRIER
INFORMATION CONTACT SGS-THOMSON

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	−0.5 to 7	V
V_I	DC Input Voltage	−0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	−0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	−65 to 150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≅ 65°C derate to 300 mW by 10 mW/°C: 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value		Unit
V_{CC}	Supply Voltage	2 to 6		V
V_I	Input Voltage	0 to V_{CC}		V
V_O	Output Voltage	0 to V_{CC}		V
T_A	Operating Temperature 74HC Series 54HC Series	− 40 to 85 −55 to 125		°C
t_r, t_f	Input Rise and Fall Time	V_{CC} 2 V	0 to 1000	ns
		V_{CC} 4.5V	0 to 500	
		V_{CC} 6 V	0 to 400	

DC SPECIFICATIONS

Symbol	Parameter	V_{CC}	Test Condition		$T_A = 25°C$ 54HC and 74HC			−40 to 85°C 74HC		−55 to 125°C 54HC		Unit
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0			1.5	—	—	1.5	—	1.5	—	V
		4.5			3.15	—	—	3.15	—	3.15	—	
		6.0			4.2	—	—	4.2	—	4.2	—	
V_{IL}	Low Level Input Voltage	2.0			—	—	0.5	—	0.5	—	0.5	V
		4.5			—	—	1.35	—	1.35	—	1.35	
		6.0			—	—	1.8	—	1.8	—	1.8	
V_{OH}	High Level Output Voltage	2.0	V_I	I_O	1.9	2.0	—	1.9	—	1.9	—	V
		4.5	V_{IH} or	−20 μA	4.4	4.5	—	4.4	—	4.4	—	
		6.0	V_{IL}		5.9	6.0	—	5.9	—	5.9	—	
		4.5		−4.0 mA	4.18	4.31	—	4.13	—	4.10	—	
		6.0		−5.2 mA	5.68	5.8	—	5.63	—	5.60	—	
V_{OL}	Low Level Output Voltage	2.0	V_{IH} or V_{IL}	20 μA	—	0	0.1	—	0.1	—	0.1	V
		4.5			—	0	0.1	—	0.1	—	0.1	
		6.0			—	0	0.1	—	0.1	—	0.1	
		4.5		4.0 mA	—	0.17	0.26	—	0.33	—	0.40	
		6.0		5.2 mA	—	0.18	0.26	—	0.33	—	0.40	
I_I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND		—	—	±0.1	—	±1	—	±1	μA
I_{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND		—	—	2	—	20	—	40	μA

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5V$, $T_A = 25°C$, $C_L = 15pF$, Input $t_r = t_f = 6ns$)

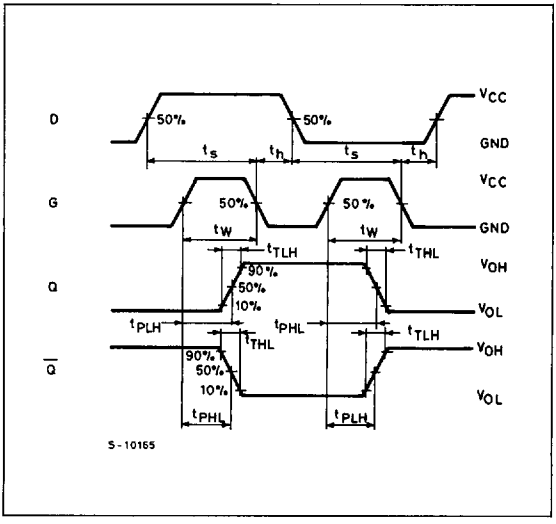
Symbol	Parameter	54HC and 74HC			Unit
		Min.	Typ.	Max.	
t_{TLH} t_{THL}	Output Transition Time		4	8	ns
t_{PLH} t_{PHL}	Propagation Delay Time (DATA-Q, $\overline{Q}$)		12	20	ns
t_{PLH} t_{PHL}	Propagation Delay Time (G-Q, $\overline{Q}$)		15	25	ns

AC ELECTRICAL CHARACTERISTICS (C_L = 50pF, Input $t_r = t_f$ = 6ns)

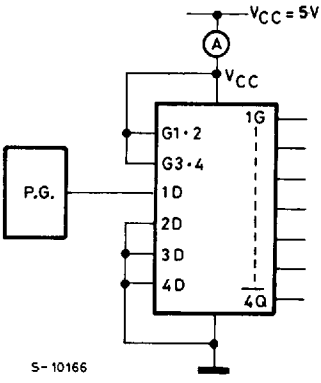
Symbol	Parameter	V_{CC}	Test Condition	T_A = 25°C 54HC and 74HC			−40 to 85°C 74HC		−55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} T_{THL}	Output Transition Time	2.0		—	30	75	—	95	—	110	ns
		4.5		—	8	15	—	19	—	22	
		6.0		—	7	13	—	16	—	19	
t_{PLH} t_{PHL}	Propagation Delay Time (DATA-Q, $\overline{Q}$)	2.0		—	60	120	—	150	—	180	ns
		4.5		—	15	24	—	30	—	36	
		6.0		—	13	20	—	26	—	31	
t_{PLH} t_{PHL}	Propagation Delay Time (G-Q, $\overline{Q}$)	2.0		—	76	145	—	180	—	218	ns
		4.5		—	19	29	—	36	—	44	
		6.0		—	16	25	—	31	—	38	
$t_{W(H)}$	Minimum Pulse Width (G)	2.0		—	30	75	—	95	—	110	ns
		4.5		—	8	15	—	19	—	22	
		6.0		—	7	13	—	16	—	19	
t_s	Minimum Set-Up Time	2.0		—	5	50	—	65	—	75	ns
		4.5		—	1	10	—	13	—	15	
		6.0		—	1	9	—	11	—	13	
t_h	Minimum Hold Time	2.0		—	—	25	—	30	—	40	ns
		4.5		—	—	5	—	6	—	8	
		6.0		—	—	5	—	6	—	7	
C_{IN}	Input Capacitance			—	5	10	—	10	—	10	pF
C_{PD} (*)	Power Dissipation Capacitance			—	48	—	—	—	—	—	pF

Note (*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load.

SWITCHING CHARACTERISTICS TEST CIRCUIT



TEST CIRCUIT I_{CC} (Opr)



INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.